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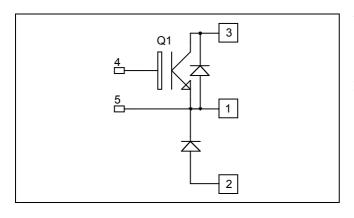
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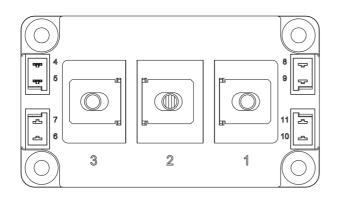
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Buck Chopper Trench + Field Stop IGBT3 Power Module





$V_{CES} = 1700V$

APTGT300SK170D3G

$I_{\rm CES} = 300 {\rm A}$ @ Tc = 80°C

Application

- AC and DC motor control
- Switched Mode Power Supplies

Features

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- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- High level of integration
- M6 power connectors

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage		1700	V
I _C	Continuous Collector Current	$T_C = 25^{\circ}C$	400	
1 _C	Continuous Conector Current	$T_C = 80^{\circ}C$	300	А
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	600	
V_{GE}	Gate – Emitter Voltage		± 20	V
PD	Maximum Power Dissipation	$T_C = 25^{\circ}C$	1470	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	600A@1650V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics								
Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit		
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1700V$				3	mA	
V	Collector Emitter on Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		2.0	2.5	V	
V _{CE(on)}	Conector Emitter on Voltage	$I_{\rm C} = 300 {\rm A}$ $T_{\rm j} = 125^{\circ}{\rm C}$		2.4		v		
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 12 \text{ mA}$		5.2	5.8	6.4	V	
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA	

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V, V_{CE} = 25V$ f = 1MHz			27		nF
C _{res}	Reverse Transfer Capacitance				0.9		III.
Q _G	Gate charge	$V_{GE}=\pm 15V, I_{C}=300A$ $V_{CE}=900V$			3.5		μC
T _{d(on)}	Turn-on Delay Time	Inductive Switch	ning (25°C)		280		
Tr	Rise Time	$V_{GE} = \pm 15V$			80		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 900V$ $I_{C} = 300A$ $R_{G} = 4.7\Omega$			850		ns
$T_{\rm f}$	Fall Time				120		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15V$ $V_{Bus} = 900V$ $I_C = 300A$ $R_G = 4.7\Omega$			300		ns
Tr	Rise Time				100		
T _{d(off)}	Turn-off Delay Time				1000		
T_{f}	Fall Time				200		
Eon	Turn On Energy	$V_{Bus} = 900V$ $T_i = 12$	$T_i = 25^{\circ}C$		71		
Lon			$T_{i} = 125^{\circ}C$		105		mJ
E _{off}	Turn Off Energy	$I_{\rm C} = 300 {\rm A}$	$T_j = 25^{\circ}C$		64		1113
Loff	Turn Off Energy	$R_G = 4.7\Omega$	$R_{\rm G} = 4.7\Omega \qquad \qquad T_{\rm i} = 125^{\circ}{\rm C}$		94		
I _{sc}	Short Circuit data	$V_{GE} \le 15V$; $V_{Bus} = 1000V$ $t_p \le 10\mu s$; $T_1 = 125^{\circ}C$			1200		А

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			1700			V
т	Maximum Reverse Leakage Current	V _R =1700V	$T_j = 25^{\circ}C$			750	۸
I _{RRM}			$T_{j} = 125^{\circ}C$			1000	μA
I _F	DC Forward Current		$Tc = 80^{\circ}C$		300		А
V _F	Diode Forward Voltage	$I_F = 300A$	$T_j = 25^{\circ}C$		1.8	2.2	V
▼ F			$T_{i} = 125^{\circ}C$		1.9		•
t _{rr}	Reverse Recovery Time	$I_{\rm F} = 300 {\rm A}$ $V_{\rm R} = 900 {\rm V}$ ${\rm di/dt} = 3500 {\rm A}/\mu {\rm s}$	$T_j = 25^{\circ}C$		385		ns
			$T_{j} = 125^{\circ}C$		490		115
Q _{rr}	Reverse Recovery Charge		$T_j = 25^{\circ}C$		76		uС
			$T_{j} = 125^{\circ}C$		124		μC
E _{rr}	Reverse Recovery Energy		$T_j = 25^{\circ}C$		35		mJ
		$T_j = 125^{\circ}C$			70		1113

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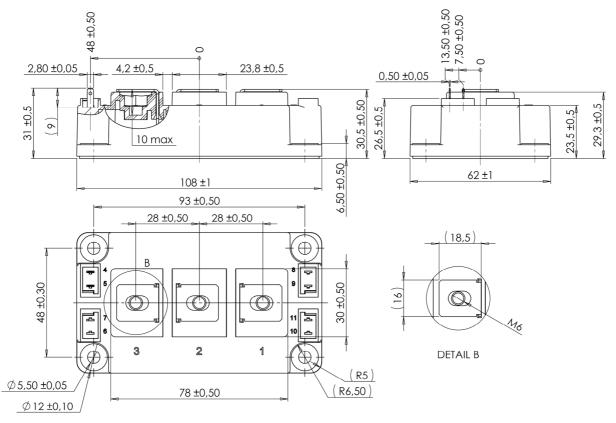


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Thermal and package characteristics

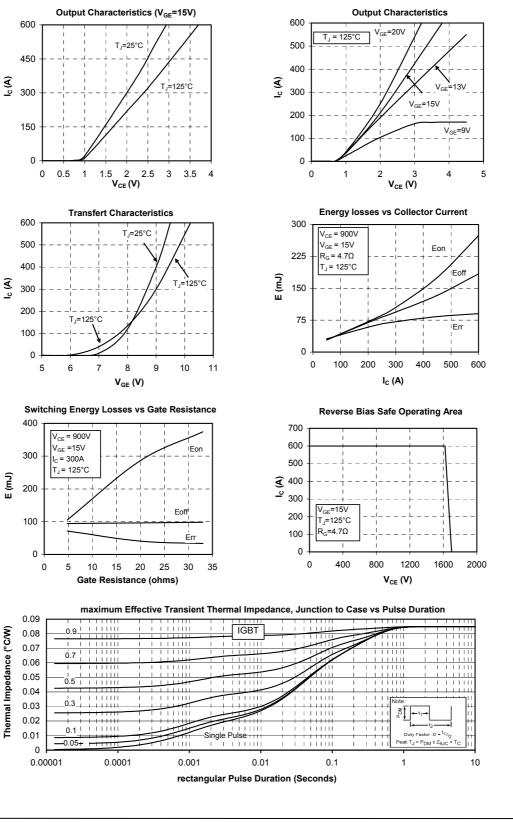
Symbol	Characteristic			Min	Тур	Max	Unit
D	R _{thJC} Junction to Case Thermal Resistance IGBT Diode				0.085	°C/W	
R _{th} JC			Diode			0.13	C/ W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T _J	Operating junction temperature range			-40		150	
T _{STG}	Storage Temperature Range			-40		125	°C
T _C	Operating Case Temperature			-40		125	
Torque	Mounting torque	For terminals	M6	3		5	N.m
		To Heatsink	M6	3		5	19.111
Wt	Package Weight					350	g

D3 Package outline (dimensions in mm)





Typical Performance Curve



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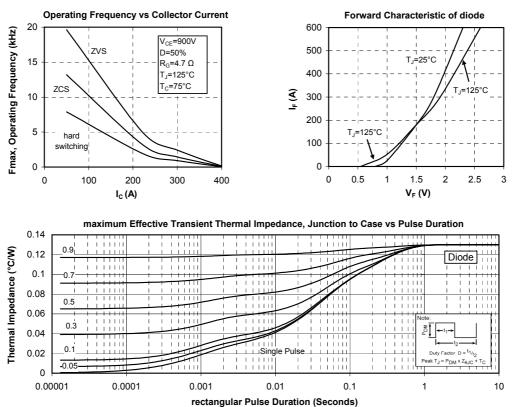
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